

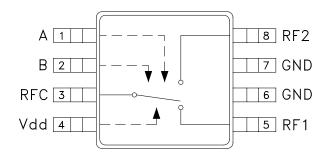


# Typical Applications

The HMC574MS8 / HMC574MS8E is ideal for:

- Cellular/3G Infrastructure
- Private Mobile Radio Handsets
- WLAN, WIMAX & WiBro
- Automotive Telematics
- Test Equipment

### **Functional Diagram**



# HMC574MS8 / 574MS8E

# GaAs MMIC 5 WATT T/R SWITCH DC - 3 GHz

#### Features

Low Insertion Loss: 0.3 dB High Third Order Intercept: +65 dBm Isolation: 30 dB Single Positive Supply: +3 to +10V SMT Package: MSOP8 Included in the HMC-DK005 Designer's Kit

### **General Description**

The HMC574MS8 & HMC574MS8E are low-cost SPDT switches in 8-lead MSOP packages for use in transmit/receive applications which require very low distortion at high incident power levels. The device can control signals from DC to 3.0 GHz and is especially suited for Cellular/3G infrastructure, WiMAX and WiBro applications with only 0.3 dB typical insertion loss. The design provides 5 watt power handling performance and +65 dBm third order interceptat +8 Volt bias. RF1 and RF2 are reflective shorts when "Off". Control inputs A & B are compatible with CMOS and some TTL logic families. These products are form, fit and function replacements for HMC174MS8 & HMC174MS8E while offering superior electrical performance.

## **Electrical Specifications**,

#### $T_A = +25^{\circ}$ C, Vctl = 0/+5 Vdc, Vdd = +5 Vdc (Unless Otherwise Stated), 50 Ohm System

Parameter		Frequency	Min.	Тур.	Max.	Units
Insertion Loss		DC - 1.0 GHz DC - 2.0 GHz DC - 2.5 GHz DC - 3.0 GHz		0.25 0.3 0.4 0.5	0.5 0.6 0.7 0.8	dB dB dB dB
Isolation		DC - 1.0 GHz DC - 2.0 GHz DC - 2.5 GHz DC - 3.0 GHz	26 24 21 16	30 28 25 20		dB dB dB dB
Return Loss		DC - 1.0 GHz DC - 2.0 GHz DC - 2.5 GHz DC - 3.0 GHz		35 25 18 16		dB dB dB dB
Input Power for 1dB Compression	Vctl = 0/+3V Vctl = 0/+5V Vctl = 0/+8V	0.5 - 3.0 GHz	33 35 37	36 38 39		dBm dBm dBm
Input Third Order Intercept (Two-tone Input Power = +27 dBm Each Tone)	Vctl = 0/+3V Vctl = 0/+5V Vctl = 0/+8V	0.5 - 3.0 GHz		55 63 65		dBm dBm dBm
Switching Characteristics		DC - 3.0 GHz				
ton, top	tRISE, tFALL (10/90% RF) FF (50% CTL to 10/90% RF)			80 120		ns ns

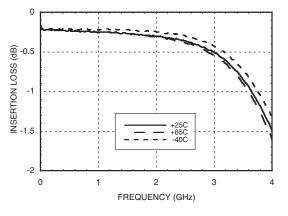
For price, delivery, and to place orders, please contact Hittite Microwave Corporation: 20 Alpha Road, Chelmsford, MA 01824 Phone: 978-250-3343 Fax: 978-250-3373 Order On-line at www.hittite.com



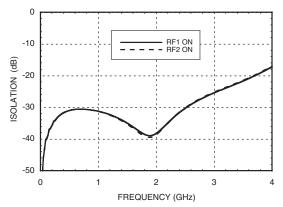


## GaAs MMIC 5 WATT T/R SWITCH DC - 3 GHz

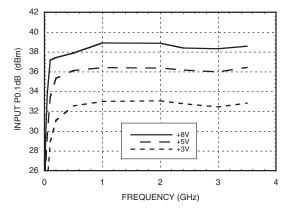
#### **Insertion Loss**



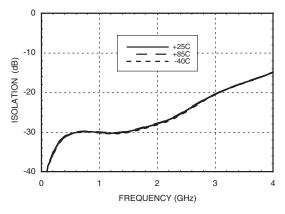
### **RF1 to RF2 Isolation**



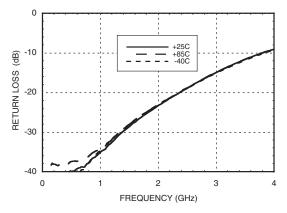
Input P0.1dB vs. Vdd



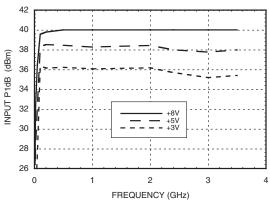
### Isolation Between RFC & RF1/RF2



#### Return Loss





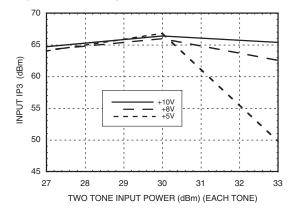


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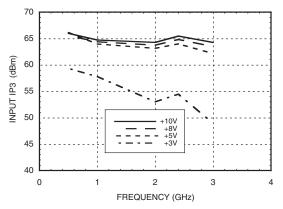




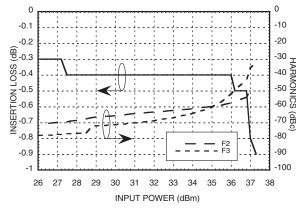
#### Input IP3 vs. Input Power @ 900 MHz



### Input Third Order Intercept

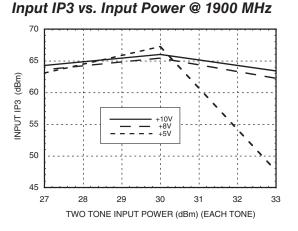




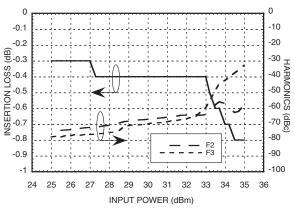


HMC574MS8 / 574MS8E

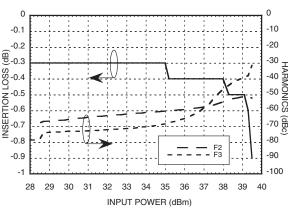
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#### 2nd & 3rd Harmonics @ 900 MHz Vdd = +3 Volts





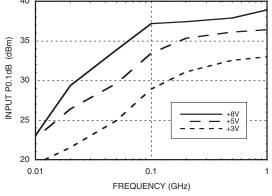






# GaAs MMIC 5 WATT T/R SWITCH DC - 3 GHz

# Input P0.1dB vs. Vdd



## Absolute Maximum Ratings

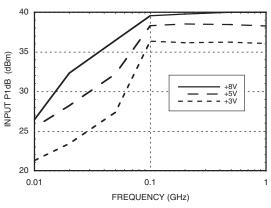
Max. Input Power V <sub>dd</sub> = 0/+8V	0.5 - 2.5 GHz	39 dBm	
Bias Voltage Rang	e (Vdd)	-0.2 to +12 Vdc	
Control Voltage Ra	inge (A & B)	-0.2 to +Vdd Vdc	
Hot Switching Power Level V <sub>dd</sub> = +8V		39 dBm	
Channel Temperature		150 °C	
Continuous Pdiss (T= + 85 °C) (derate 10 mW/°C above 85 °C)		0.65W	
Thermal Resistance		100 °C/W	
Storage Temperature		-65 to +150 °C	
Operating Temperature		-40 to +85 °C	
ESD Sensitivity (HBM)		Class 1A	

DC Blocks are required at ports RFC, RF1 and RF2



#### ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

#### Input P1dB vs. Vdd



## **Bias Voltage & Current**

Vdd (Vdc)	Typical Idd (µA)
+3	2
+5	10
+8	40

## **Control Voltages**

State	Bias Condition
Low	0 to +0.2 Vdc @ 10 μA Typical
High	Vdd ± 0.2 Vdc @ 10 µA Typical

## Truth Table

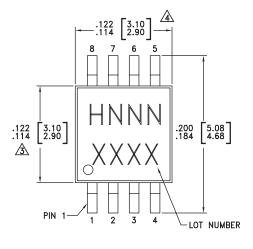
Control Input (Vctl)		Signal Path State	
A	В	RFC to RF1	RFC to RF2
High	Low	Off	On
Low	High	On	Off

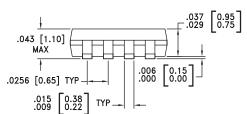


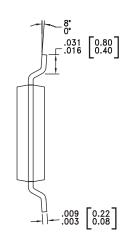


## GaAs MMIC 5 WATT T/R SWITCH DC - 3 GHz

### **Outline Drawing**







#### NOTES:

1. LEADFRAME MATERIAL: COPPER ALLOY

2. DIMENSIONS ARE IN INCHES [MILLIMETERS]

A DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.15mm PER SIDE.

A DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.25mm PER SIDE.

5. ALL GROUND LEADS MUST BE SOLDERED TO PCB RF GROUND.

## Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking <sup>[3]</sup>
HMC574MS8	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 <sup>[1]</sup>	H574 XXXX
HMC574MS8E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 <sup>[2]</sup>	<u>H574</u> XXXX

[1] Max peak reflow temperature of 235  $^\circ\text{C}$ 

[2] Max peak reflow temperature of 260 °C

[3] 4-Digit lot number XXXX



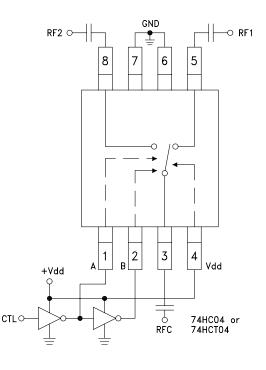
## GaAs MMIC 5 WATT T/R SWITCH DC - 3 GHz



### **Pin Descriptions**

Pin Number	Function	Description	Interface Schematic
1	А	See truth table and control voltage table.	R
2	В	See truth table and control voltage table.	⊥ c
3, 5, 8	RFC, RF1, RF2	This pin is DC coupled and matched to 50 Ohm. Blocking capacitors are required.	
4	Vdd	Supply Voltage.	
6, 7	GND	This pin must be connected to RF/DC ground.	

## **Typical Application Circuit**



#### Notes:

- 1. Set logic gate and switch Vdd = +3V to +5V and use HCT series logic to provide a TTL driver interface.
- Control inputs A/B can be driven directly with CMOS logic (HC) with Vdd of +3 to +8 Volts applied to the CMOS logic gates and to pin 4 of the RF switch.
- 3. DC Blocking capacitors are required for each RF port as shown. Capacitor value determines lowest frequency of operation.
- 4. Highest RF signal power capability is achieved with V set to +10V. The switch will operate properly (but at lower RF power capability) at bias voltages down to +3V.

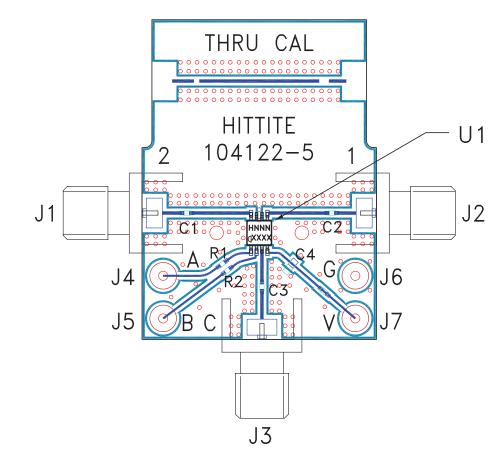


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## GaAs MMIC 5 WATT T/R SWITCH DC - 3 GHz

### **Evaluation Circuit Board**





## List of Materials for Evaluation PCB 104124 [1]

Item	Description
J1 - J3	PCB Mount SMA RF Connector
J4 - J7	DC Pin
C1 - C3	100 pF capacitor, 0402 Pkg.
C4	10,000 pF capacitor, 0603 Pkg.
R1, R2	100 Ohm resistor, 0402 Pkg.
U1	HMC574MS8 / HMC574MS8E T/R Switch
PCB <sup>[2]</sup>	104122 Evaluation PCB

Reference this number when ordering complete evaluation PCB
Circuit Board Material: Rogers 4350

The circuit board used in the final application should be generated with proper RF circuit design techniques. Signal lines at the RF port should have 50 ohm impedance and the package ground leads and package bottom should be connected directly to the ground plane similar to that shown above. The evaluation circuit board shown above is available from Hittite Microwave Corporation upon request.



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# HMC574MS8 / 574MS8E

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